



Parameter Identification of Pressure Sensors at Wafer Level

MEMUNITY-Workshop
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Outline

- ▶ **Framework & Motivation**
- ▶ **Investigated Pressure Sensor Types**
 - Absolute pressure sensors
 - Relative pressure sensors
- ▶ **Wafer Level Testing Approach**
- ▶ **Identification Algorithm/System**
 - FE modeling
- ▶ **Measurements & Identification Results**
- ▶ **Summary & Outlook**

Framework & Motivation

- ▶ BMBF funded project PARTEST (2005-2007)
 - „Measurement and Test Equipment for Determination of Production Relevant Parameters of Microsystems on Wafer-Level“
- ▶ Motivation: Significant cost reduction by detection of faulty sensors before the subsequent packaging and assembling steps
- ▶ Project partner:



Equipment manufacturers



MEMS companies

BOSCH



ELMOS
Semiconductor AG



FAB

Research institutes



Fraunhofer Institut
Werkstoffmechanik



Fraunhofer Institut
Siliziumtechnologie

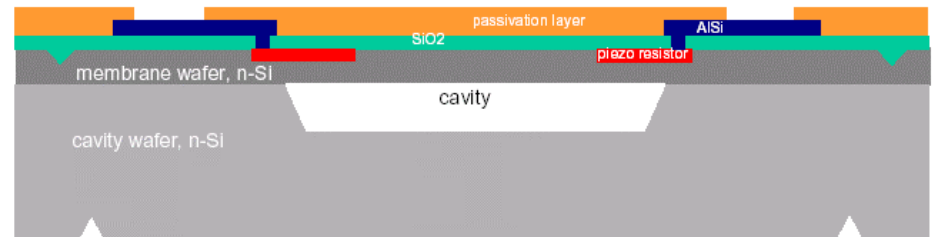


Fraunhofer Institut
Zuverlässigkeit und
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Pressure Sensors

▶ Absolute pressure sensors

- Technology: backgrinded membrane wafer is bonded on a cavity wafer
- Quadratic membrane
- Varying parameter: membrane thickness



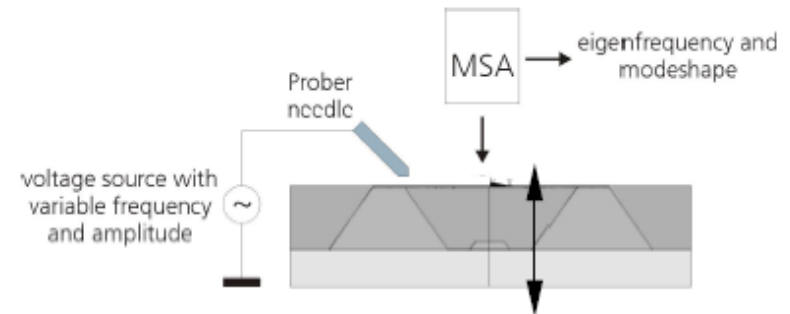
Absolute pressure sensor cross section

▶ Relative pressure sensors

- 3 varying parameter (x/y membrane size, thickness)

Wafer Level Testing Approach

- ▶ Approach: Online parameter identification by optically measured out-of-plane modal frequencies
- ▶ Electrostatic excitation of modal frequencies
- ▶ FE simulation parameter matrix is basis of identification core
- ▶ Two test modi
 - Characterization – close grid of laser measurement points
 - Go/nogo test – minimum number of laser measurement points

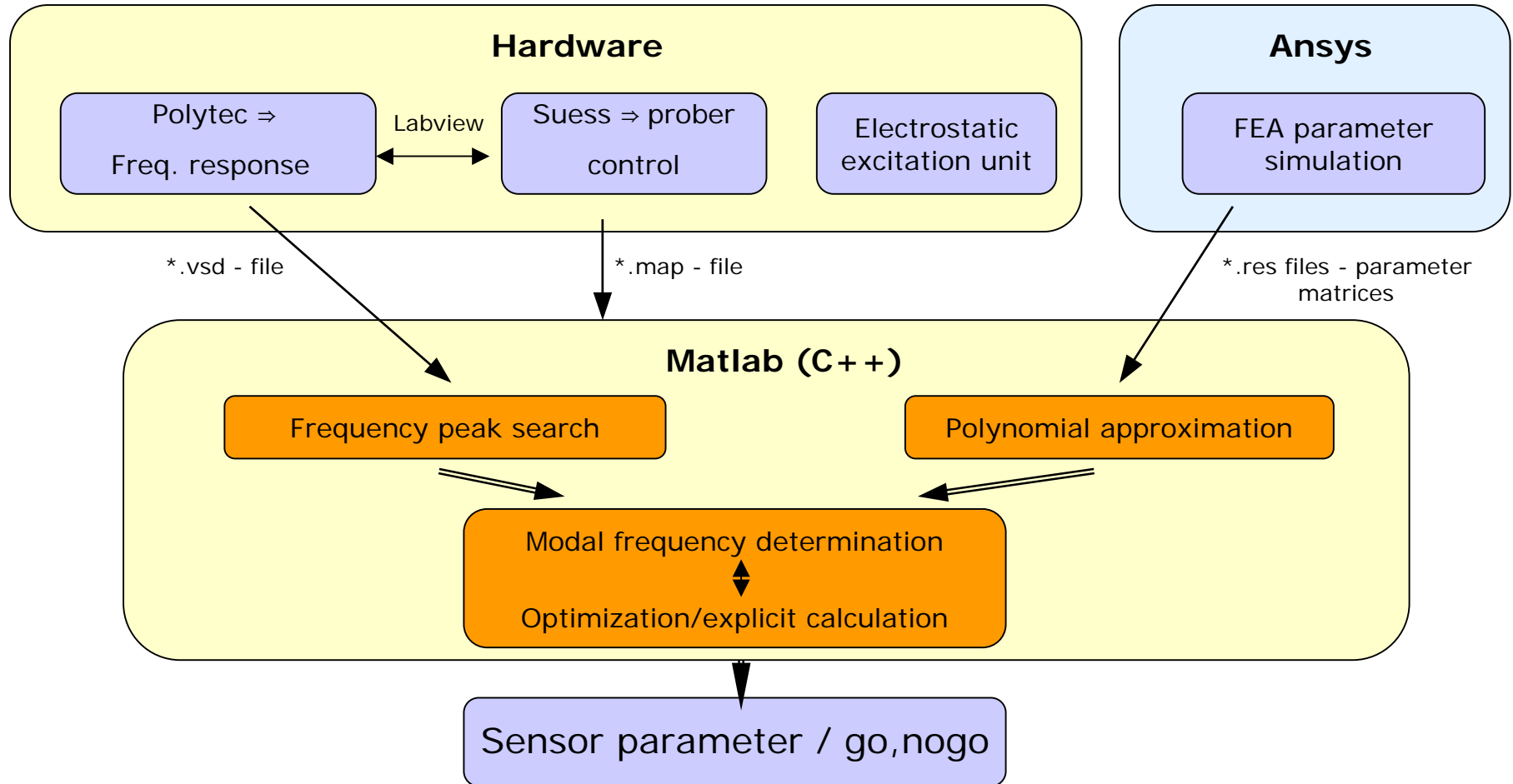


Measurement principle



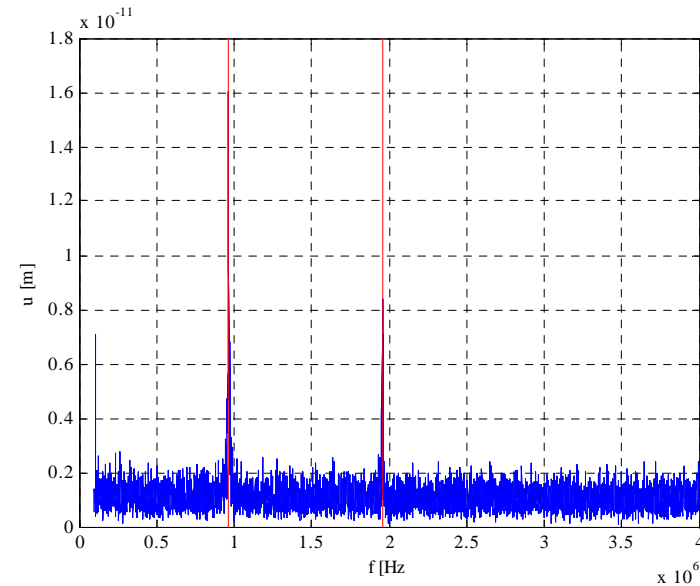
Measurement setup

Parameter Identification System



Parameter Identification System II

- **Peak picking**
 - Automatically peak identification by defined minimum/maximum peak width
- **Polynomial approximation**
 - User specified parameters: relative and absolute accuracy
 - Polynomial degree is automatically determined
- **Identification unit**
 - User specified parameter: normed IAE (Identification Accuracy Estimation)
- **Feedback to model/simulation quality**
 - ⇒ Polynomial approximation cannot be reached (including oscillation)
 - ⇒ IAE distribution on wafer follows a function instead of a stocastic distribution



Example of frequency response (absolute pressure sensor, 500x500 μ m)

Identification Accuracy Estimation (IAE)

⇒ Introduction of term IAE

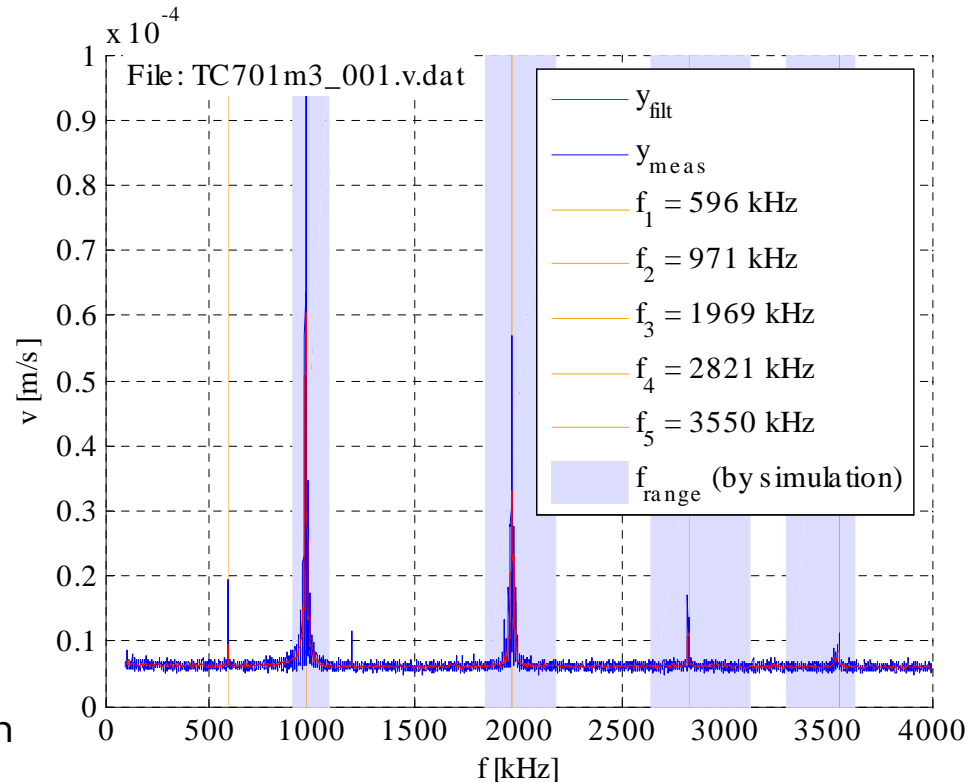
- Motivation: detection of
 - **Inaccurate model**
 - **Faulty die**
- Example (absolute pressure sensor): 3 relevant modal frequencies ($f_2=971\text{kHz}$, $f_3=1969\text{kHz}$, $f_4=2821\text{kHz}$)



1 free parameter, 3 modal frequencies ⇒ 3 membrane thicknesses ($z_1 - z_3$)

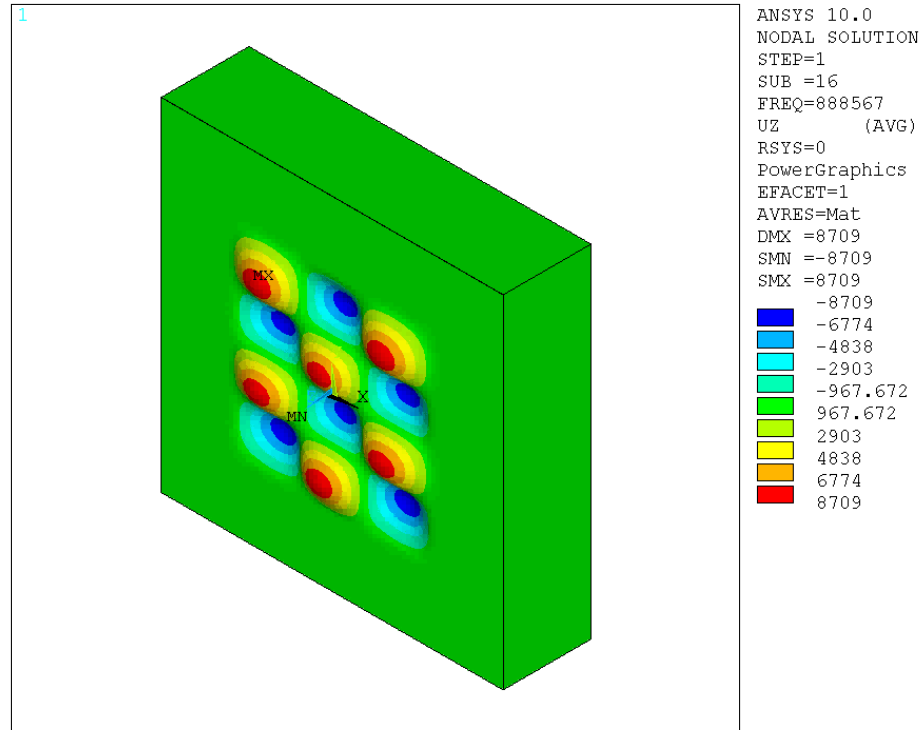


Identification Accuracy Estimation
 $IAE = \max(z_i) - \min(z_i)$



FE Modeling

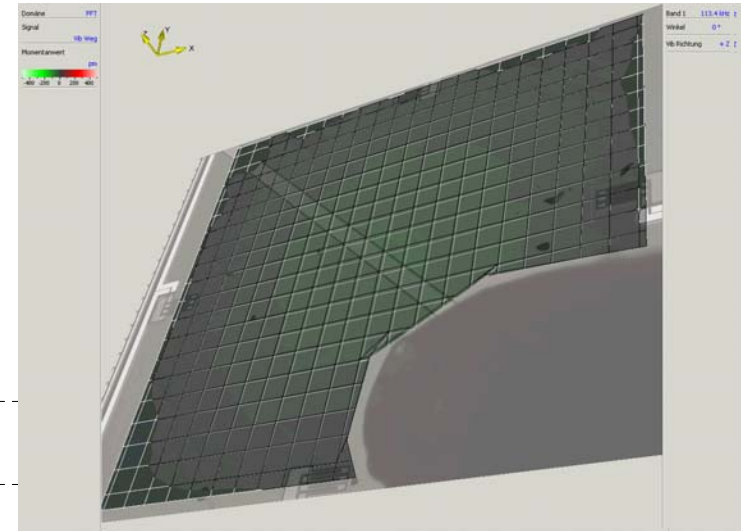
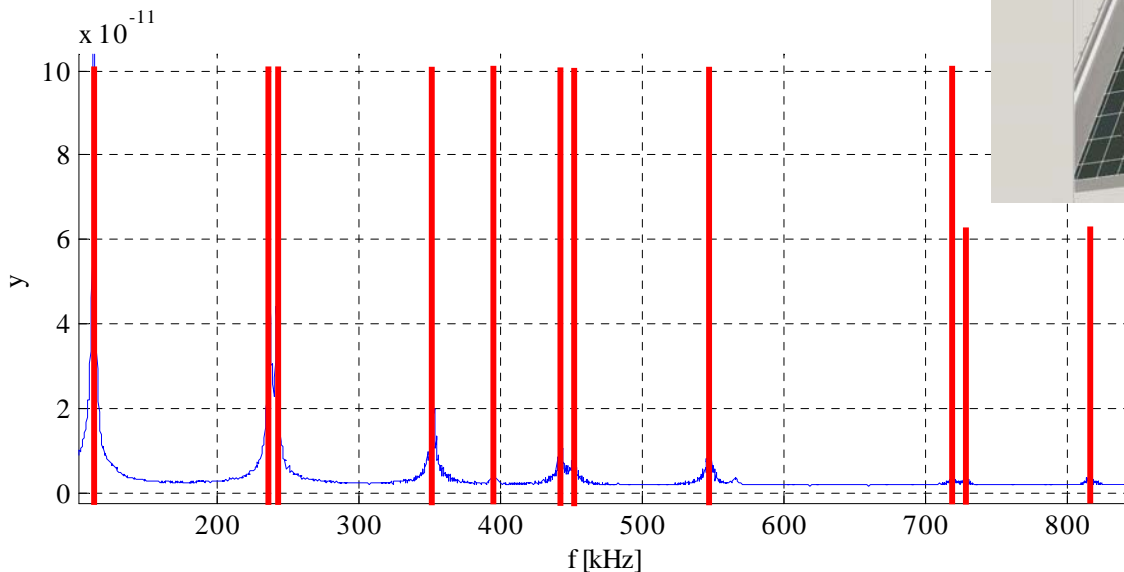
- ▶ Prestressed modal analysis of absolute and relative pressure sensors up to 11th modal frequencies
 - Thermal induced stress
 - Ambient pressure
- ▶ Parameter simulations modal frequency versus membrane parameters
- ▶ Static analysis including sensitivity calculation



Relative pressure sensor - simulation of the 11th modal frequency

Relative Pressure Sensor Measurements

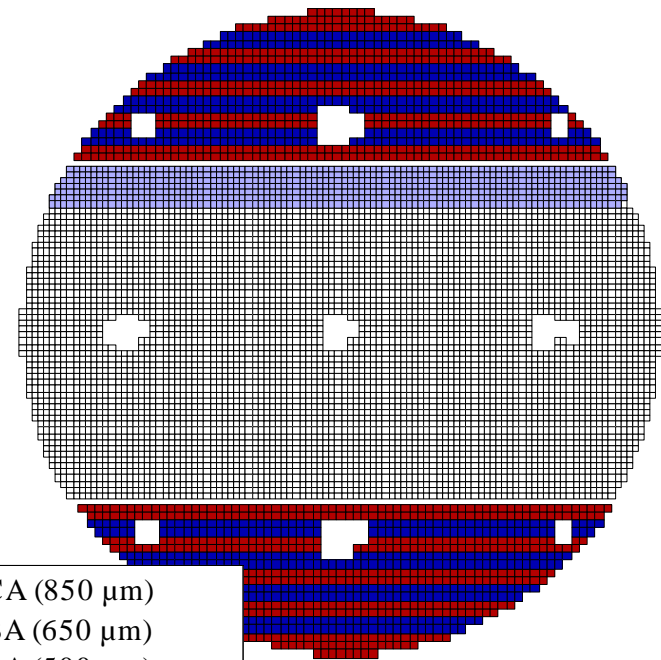
- Measurement and identification up to 10 modal frequencies



Pressure sensor mode shapes generated by Polytec PSV software

Absolute Pressure Sensor – Parameter Identification

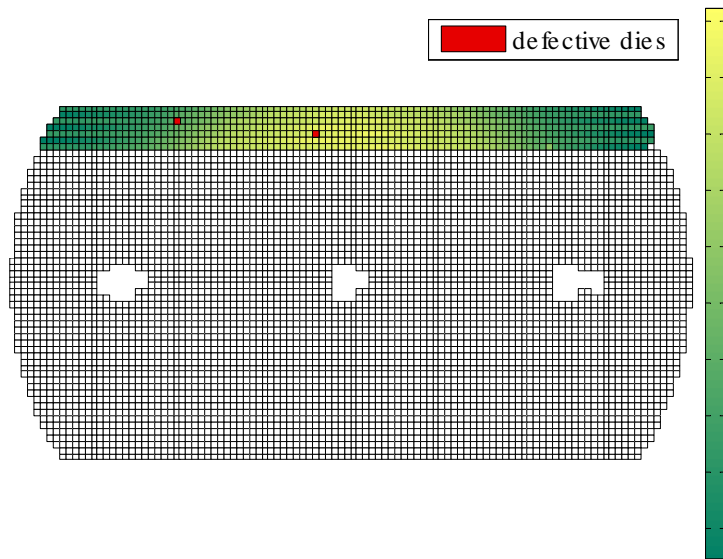
- ▶ Absolute pressure sensor with 3 different membrane sizes (500x500, 650x650, 850x850)
- ▶ Go/nogo test based on 2 criteria
 - Membrane thickness is within the spec
 - IAE is within the user defined spec ($<0.4\mu\text{m}$)



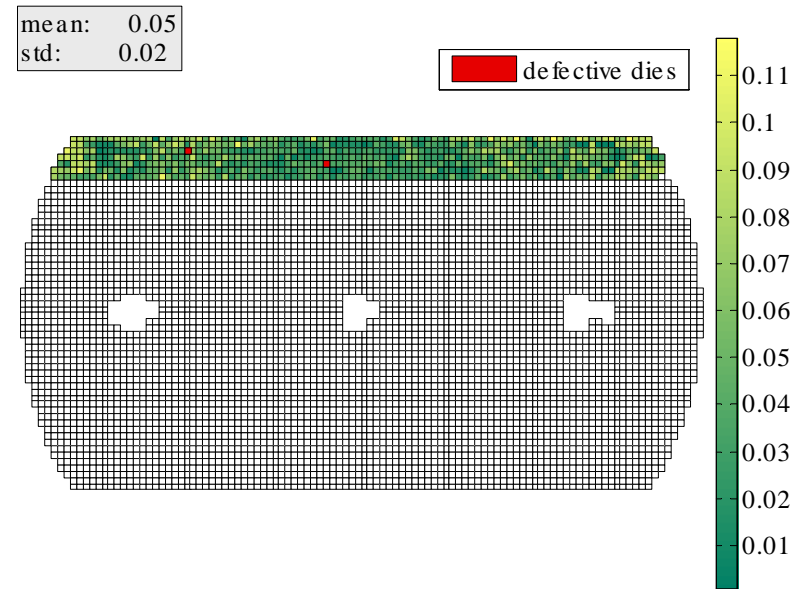
Red	TC701CA (850 μm)
Blue	TC701BA (650 μm)
Light Blue	TC701AA (500 μm)
White	TC701AA (not measured)

Parameter Identification Results

- Membrane size: 500x500 μm



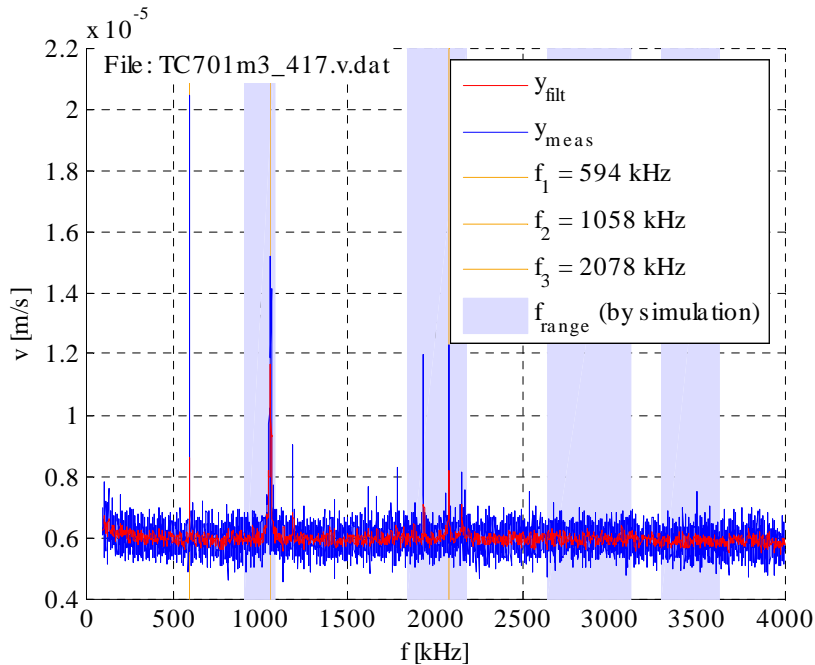
Mean value of identified membrane thicknesses



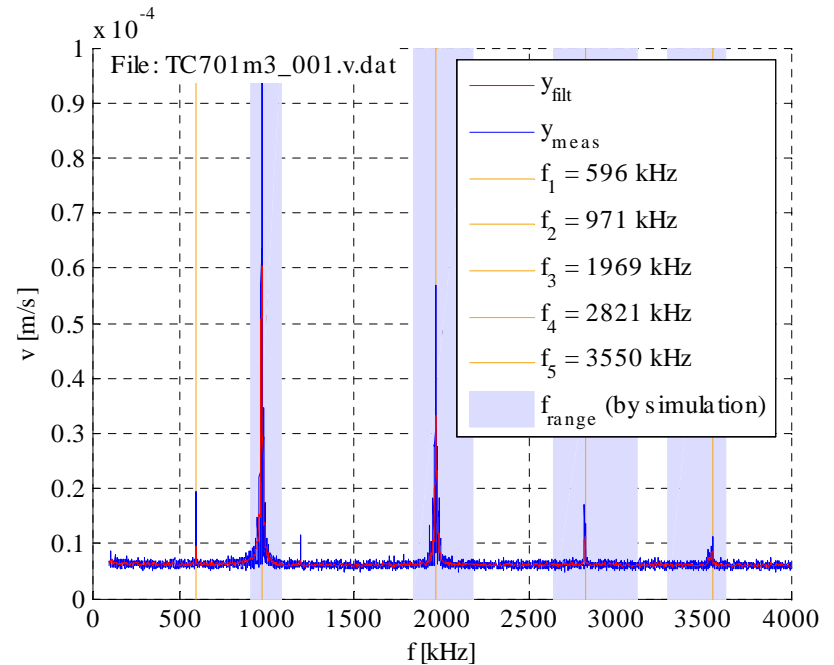
Difference between the largest and the smallest identified membrane thickness (IAE in microns)

Parameter Identification Results

- Usage of IAE to identify wrong dies



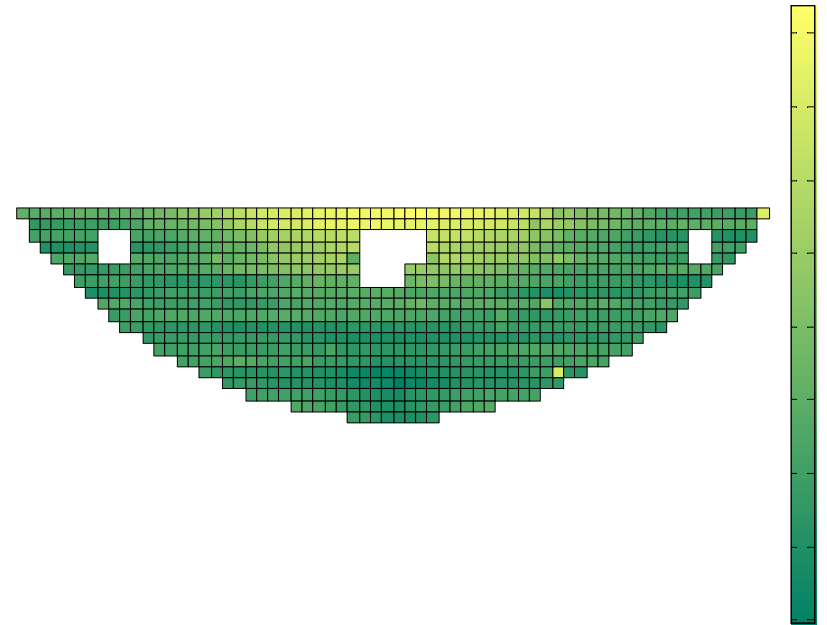
Die marked by identification as irregular



Regular die

Parameter Identification Results

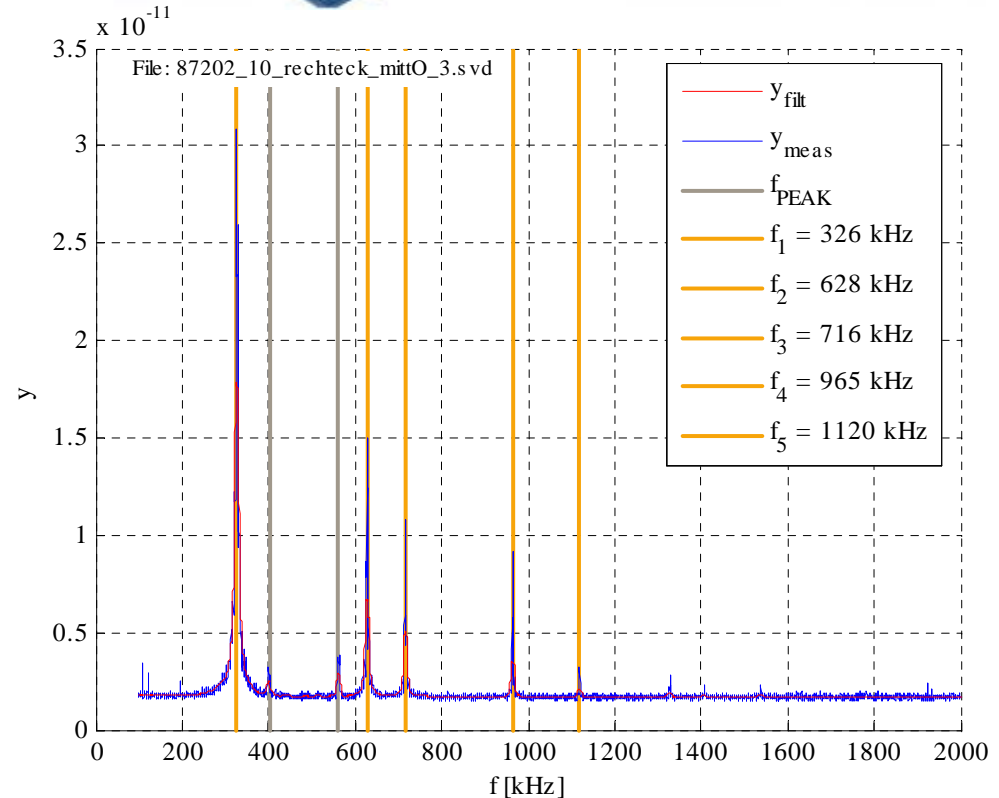
- ▶ IAE of sensor types
 - 500x500 μm : 110nm
 - 650x650 μm : <300nm
 - 850x850 μm : <400nm
- ▶ Result: model improvement of larger membranes
 - Optimization of prestress parameters



Mean value of identified membrane thicknesses
(membrane size 650x650 and 850x850)

Parameter Identification of Rectangular Membranes

- Absolute pressure sensor test structures with rectangular membranes
- Varying parameters:
 - Membrane thickness (15-25 μm)
 - Membrane size in y (800-900 μm , Note: x size is fixed)
- Note: Peaks are not obligatory modal frequencies!
- Result:
 - $X = (811.0 \mu\text{m}, 18.09 \mu\text{m})$
 - $IAE = (6.4 \mu\text{m}, 0.26 \mu\text{m})$



Parameter Identification of Relative Pressure Sensors

- Usage up to 8 modal frequencies for the identification of 3 sensor parameters.

Die number	1	2	3	4	5
Membrane thickness	14.2	13.97	14.10	14.54	13.56
IAE	0.27	0.26	0.17	0.22	0.32
X size	1302.1	1298.2	1303.1	1295.3	1302.1
IAE	4.2	9.1	12.2	13.1	8.3
Y size	1304.2	1306.3	1302.1	1298.4	1299.3
IAE	5.2	8.9	5.9	11.2	12.1



Summary & Outlook

Summary

- Vibrometer, prober and excitation unit permits the optical measurement of modal frequencies up to 2.5 MHz
- Automatic online identification of up to 3 pressure sensor parameters within 3 seconds

Outlook

- Static measurements of deformation and sensitivity – correlation of dynamic and static identification results
- Expansion of the approach to further sensor types (e.g. stress identification of IR sensors)
- Sensitivity analysis
- Reduction of measurement time to 1 second (software/hardware)



Acknowledgements

- ▶ The works are done within the public research project PAR-TEST which is funded by the German Federal Ministry of Education and Research (BMBF) (contract 16SV1941).
- ▶ The measurements were enabled with the gratefully acknowledged support of the project partners Polytec GmbH Waldbronn, the Suss Microtec GmbH Sacka and the Fraunhofer IZM Chemnitz as well as XFab AG Erfurt.



Thanks for your attention!

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